

2009 International Symposium on VLSI Technology, Systems, and Applications

(VLSI-TSA)

**Hsinchu, Taiwan
27 – 29 April 2009**



IEEE Catalog Number: CFP09846-PRT
ISBN: 978-1-4244-2784-0

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IEEE Catalog Number:	CFP09846-PRT
ISBN 13:	978-1-4244-2784-0
ISSN:	1930-885X

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TABLE OF CONTENTS

PLENARY SESSION

Has The Sun Finally Risen on Photovoltaics?	1
<i>Mark Pinto</i>	
The Future of Semiconductor Industry - A Foundry's Perspective	2
<i>Fang-Churng Tseng</i>	
From Living Faster to Living Better	3
<i>René Penning de Vries</i>	
Carrier Transport and Stress Engineering in Advanced Nanoscale MOS Transistors	5
<i>Ken Uchida</i>	

SESSION 1: PROCESS MODULE

The Impact on Device Characteristics with STI Formed by Spin-on Dielectric in High Density NAND Flash Memory	7
<i>W. Z. Wong, J. J. Fan, J. D. Jiang, C. H. Huang, C. Y. Chen, H. H. Chen, C.C. Hsu, Rex Young, P. Y. Wang, H. Fujita, H. Kobayashi</i>	
Properties of Very Thin Adenine Layer with High Inhibition for 32nm Node Cu/Low-K Interconnection	9
<i>M. Hara, H. Aoki, T. Masuzumi, D. Watanabe, C. Kimura, T. Sugino</i>	
Boron Carbon Nitride Film Containing Hydrogen for 22nm Node Low-K Interconnection	11
<i>Hidemitsu Aoki, Takuroh Masuzumi, Makoto Hara, Daisuke Watanabe, Chiharu Kimura, Takashi Sugino</i>	
Ge Shallow Junction Formation by As implantation and Flash Lamp Annealing	13
<i>Kosei Osada, Tetuya Fukunaga, Kentaro Shibahara</i>	
Impact of Lithography Variations on Advanced CMOS Devices	15
<i>J. Lorenz, C. Kampen, A. Burenkov, T. Fühner</i>	

SESSION 2: STRAIN TECHNOLOGY

Stress-Enhancement Technique in Narrowing NMOSFETs with Damascene-Gate Process and Tensile Liner	17
<i>S. Mayuzumi, S. Yamakawa, Y. Tatehita, M. Tsukamoto, H. Wakabayashi, T. Ohno, N. Nagashima</i>	
Additive Mobility Enhancement and Off-State Current Reduction in SiGe Channel pMOSFETs with Optimized Si Cap and High-k Metal Gate Stacks	19
<i>Jungwoo Oh, Prashant Majhi, Raj Jammy, Raymond Joe, Anthony Dip, Takuya Sugawara, Yasushi Akasaka, Takanobu Kaitsuka, Tsunetoshi Arikado, Masayuki Tomoyasu</i>	
Dopant and Thermal Interaction on SPE Formed SiC for NMOS Performance Enhancement	21
<i>P. W. Liu, T. F. Kuo, C. I. Li, Y. R. Wang, R. M. Huang, C. H. Tsai, C. T. Tsai, G. H. Ma</i>	
Successful Integration Scheme of Cost Effective Dual Embedded Stressor Featuring Carbon Implant and Solid Phase Epitaxy for High Performance CMOS	23
<i>M. Nishikawa, K. Okabe, K. Ikeda, N. Tamura, H. Maekawa, M. Umeyama, H. Kurata, M. Kase, K. Hashimoto</i>	

An Investigation about the Limitation of Strained-Si Technology	25
<i>M. H. Liao, Lingyen Yeh, J. C. Lu, M. H. Yu, L. T. Wang, J. Wu, P. R. Jeng, T. L. Lee, Simon Jang</i>	

SESSION 3: NON-VOLATILE MEMORIES

Characterization of Poly-silicon Emitter BJTs as Access Devices for Phase Change Memory	27
<i>B. Rajendran, M. Breitwisch, R. Cheek, M-H. Lee, Y-H. Shih, H-L. Lung, C. Lam</i>	
Low Current and Voltage Resistive Switching Memory Device Using Novel Cu/Ta₂O₅/W Structure	29
<i>S. Z. Rahaman, S. Maikap, C. H. Lin, T. Y. Wu, Y. S. Chen, P. J. Tzeng, F. Chen, C. S. Lai, M. J. Kao, M. J. Tsai</i>	
A Novel Multi - Nitridation ONO Interpoly Dielectric (MN-ONO) for Highly Reliable and High Performance NAND Flash Memory	31
<i>C. H. Liu, Y. M. Lin, Y. Sakamoto, R. J. Yang, D. Y. Yin, P. J. Chiang, H. C. Wei, C. Y. Ho, S. H. Chen, H. P. Hwang, C. H. Hung, S. Pittikoun, S. Aritome</i>	
Forming-free HfO₂ Bipolar RRAM Device with Improved Endurance and High Speed Operation	33
<i>Yu-Sheng Chen, Tai-Yuan Wu, Pei-Jer Tzeng, Pang-Shiu Chen, Heng-Yuan Lee, Cha-Hsin Lin, Frederick Chen, Ming-Jinn Tsai</i>	
Multi-Level Phase Change Memory Using Slow-Quench Operation: GST vs. GSST	35
<i>Der-Sheng Chao, Frederick T. Chen, Yen-Ya Hsu, Wen-Hsing Liu, Chain-Ming Lee, Chih-Wei Chen, Wei-Su Chen, Ming-Jer Kao, Ming-Jinn Tsai</i>	

SESSION 4: GREEN DEVICES (ALL INVITED TALKS)

The Standby Power Challenge: Wake-up Receivers to the Rescue	37
<i>Jan Rabaey</i>	
Realizing Steep Subthreshold Swing with Impact Ionization Transistors	38
<i>Yee-Chia Yeo</i>	
Optimizing Tunnel FET Performance – Impact of Device Structure, Transistor Dimensions and Choice of Material	40
<i>Joachim Knoch</i>	
Nanoelectromechanical Systems for Ultra-Low-Power Computing and VLSI	42
<i>Philip Feng</i>	

SESSION 5: HIGH-K/METAL GATE

Single-Metal Dual-Dielectric (SMDD) Gate-First CMOS Integration Towards Low VT and High Performance (Invited)	43
<i>L-Å Ragnarsson, T. Schram, E. Röhr, F. Sebaai, P. Kelkar, M. Wada, T. Kauerauf, M. Aoulaiche, M. J. Cho, S. Kubicek, A. Lauwers, T. Y. Hoffmann, P. P. Absil, S. Biesemans</i>	
Low Capacitance Approaches for 22nm Generation Cu Interconnect (Invited)	45
<i>T. I. Bao, H. C. Chen, C. J. Lee, H. H. Lu, S. L. Shue, C. H. Yu</i>	
A V_{FB} Tunable Single Metal Single Dielectric Approach Using As I/I into TiN/HfO₂ for 32nm Node and Beyond	51
<i>J. Petry, G. Boccardi, R. Singanamalla, C. S. Liu, K. Xiong, P. Escanes, J. L. Huguenin, J. Tseng, L. Van Nimwegen, F. Voogt, C.W.T. Bulle-Lieuwma, M. Müller</i>	

La-doped metal/High-K nMOSFET for Sub-32nm HP and LSTP Application	53
<i>C. S. Park, J. W. Yang, M. M. Hussain, C. Y. Kang, J. Huang, P. Sivasubramani, C. Park, K. Tateiwa, Y. Harada, J. Barnett, C. Melvin, G. Bersuker, P. D. Kirsch, B. H. Lee, H. H. Tseng, R. Jammy</i>	
Extending Spectroscopic Ellipsometry for Identification of Electrically Active Defects in Si/SiO₂/High-k/Metal Gate Stacks	55
<i>J. Price, G. Bersuker, P. S. Lysaght, H. H. Tseng</i>	
22nm CMOS Approaches by PVD TiN or Ti-Silicide as Metal Ga	57
<i>C. S. Liu, G. Boccardi, H. Y. Wang, C. T. Lin, J. Petry, M. Müller, Z. Li, C. Zhao, C. H. Yu</i>	
Reliability Assessment of Low V_t Metal High-k Gate Stacks for High Performance Applications	59
<i>C. D. Young, G. Bersuker, P. Khanal, C. Y. Kang, J. Huang, C. S. Park, P. Kirsch, H. H. Tseng, R. Jammy</i>	
High Performance Metal/Insulator/Metal Capacitors Using HfTiO as Dielectric	61
<i>Hsiao-Hsuan Hsu, Bing-Yue Tsui</i>	
High-K/ Metal-Gate Stack Work-function Tuning by Rare-Earth Capping Layers: Interface Dipole or Bulk Charge?	63
<i>H.Y. Yu, S.Z. Chang, M. Aoulaiche, B. Kaczer, P. Absil, C. Adelman, T. Hoffmann, S. Biesemans, C. Wann, Y. J. Mii</i>	
 <u>SESSION 6: CMOS</u>	
Scaling Challenges of MOSFET for 32nm node and Beyond (Invited)	65
<i>Yasuo Nara</i>	
P-FinFETs with Al Segregated NiSi/p⁺-Si Source/Drain Contact Junction for Series Resistance Reduction	67
<i>Mantavya Sinha, Rinus T. P. Lee, Sivasubramaniam Nandini Devi, Guo-Qiang Lo, Eng Fong Chor, Yee-Chia Yeo</i>	
Impacts of NBTI on SRAM Array with Power Gating Structure	69
<i>Hao-I Yang, Ching-Te Chuang, Wei Hwang</i>	
CMOS Technology Roadmap Projection Including Parasitic Effects	71
<i>Lan Wei, Frédéric Boeuf, Thomas Skotnicki, H. S. Philip Wong</i>	
The Device Architecture Dilemma for CMOS Technologies: Opportunities & Challenges of FinFET over Planar MOSFET	73
<i>B. Parvais, A. Mercha, N. Collaert, R. Rooyackers, I. Ferain, M. Jurczak, V. Subramanian, A. De Keersgieter, T. Chiarella, C. Kerner, L. Witters, S. Biesemans, T. Hoffman</i>	
Investigation of Low Frequency Noise in Uniaxial Strained PMOSFETs	75
<i>Jack J. Y. Kuo, William P. N. Chen, Pin Su</i>	
FDSOI CMOS with Dual Backgate Control for Performance and Power Modulation	77
<i>Jeng-Bang Yau, Jin Cai, Leathen Shi, Robert. H. Dennard, Arvind Kumar, Katherine L. Saenger, Alexander Reznicek, Paul. M. Solomon, Qiqing Ouyang, Steven Koester, Wilfried E. Haensch</i>	
Sub-32nm CMOS Technology Enhancement For Low Power Applications	79
<i>R. M. Huang, P. W. Liu, E. C. Liu, W. T. Chiang, S. H. Tsai, Jonas Tsai, Tzermin Shen, C. H. Tsai, C. T. Tsai, G. H. Ma</i>	
Highly Performant FDSOI pMOSFETs with Metallic Source/Drain	81
<i>T. Poiroux, M. Vinet, F. Nemouchi, V. Carron, Y. Morand, B. Previtali, S. Descombes, L. Tosti, O. Cueto, L. Baud, V. Balan, M. Rivoire and S. Deleonibus, O. Faynot</i>	

High-k/Metal Gate Low Power Bulk Technology - Performance Evaluation of Standard CMOS Logic Circuits, Microprocessor Critical Path Replicas, and SRAM for 45nm and Beyond	83
<i>D. G. Park, K. Stein, K. Schrufer, Y. Lee, J. P. Han, W. Li, H. Yin, C. Pacha, N. Kim, M. Ostermayr, M. Eller, S. Kim, K. Kim, S. Han, K. von Arnim, N. Moumen, M. Hatzistergos, T. Tang, R. Loesing, X. Chen, D. Jaeger, H. Zhuang, J. Chen, W. Yan, T. Kanarsky, M. Chowdhury, Jens Haetty, D. Schepis, M. Chudzik, V. Y. Theon, S. Samavedam, V. Narayanan, M. Sherony, R. Lindsay, A. Steegen, R. Divakaruni, M. Khare</i>	
NGL Overview	86
<i>Burn Lin</i>	
Double Patterning Interactions with Wafer Processing, OPC and Physical Design Flows	87
<i>Kevin Lucas</i>	
Multiple Electron Beam Maskless Lithography for High-Volume Manufacturing	88
<i>Jack J.H. Chen, S.J. Lin, T.Y. Fang, S.M. Chang, Faruk Krecinic, Burn J. Lin</i>	
Status and Challenges of Extreme UV Lithography	90
<i>Kurt Ronse, Eric Hendrickx, Mieke Goethals, Rik Jonckheere, Geert Vandenberghe</i>	
Recent Developments in NAND Flash Scaling (Invited)	92
<i>Krishna Parat</i>	
Modeling and Scaling Evaluation of Junction-Free Charge-Trapping NAND Flash Devices	94
<i>Yi-Hsuan Hsiao, Hang-Ting Lue, Kuang-Yeu Hsieh, Rich Liu, Chih-Yuan Lu</i>	
Gate Last MOSFET with Air Spacer and Self-Aligned Contacts for Dense Memories	96
<i>Jemin Park, Chenming Hu</i>	
A Physics-Based Compact Model of Quantum-Mechanical Effects for Thin Cylindrical Si-Nanowire MOSFETs	98
<i>Bastien Cousin, Olivier Rozeau, Marie-Anne Jaud, Jalal Jomaah</i>	
A New Technique to Extract the Gate Bias Dependent S/D Series Resistance of Sub-100nm MOSFETs	100
<i>Dominique Fleury, Antoine Cros, Grégory Bidal, Hugues Brut, Emmanuel Josse, Gérard Ghibaudo</i>	
Analytical Modeling of Accumulation-Mode Suspended-Gate MOSFET and Process Challenges for Very Low Operating Power Devices	102
<i>M. Collonge, M. Vinet, M. Ribeiro, J.-M. Pedini, B. Previtali, T. Ernst, S. Bécu, G. Ghibaudo</i>	
A New Robust Non-local Algorithm for Band-to-band Tunneling Simulation and its Application to Tunnel-FET	104
<i>C. Shen, L. T. Yang, E. H. Toh, C. H. Heng, G. S. Samudra, Y. C. Yeo</i>	
Investigation of Static Noise Margin of Ultra-Thin-Body SOI SRAM Cells in Subthreshold Region using Analytical Solution of Poisson's Equation	106
<i>Vita Pi-Ho Hu, Yu-Sheng Wu, Ming-Long Fan, Pin Su, Ching-Te Chuang</i>	
The Promise and Implementation of Three Dimensional Integration (Invited)	108
<i>Subramanian Iyer</i>	
Optimization of the Channel Lateral Strain Profile for Improved Performance of Multi-Gate MOSFETs	109
<i>L. De Michielis, K. E. Moselund, D. Bouvet, P. Dobrosz, S. Olsen, A. O'Neill, L. Lattanzio, M. Najmzadeh, L. Selmi, A. M. Ionescu</i>	
A Novel Double-Gated Nanowire TFT and Investigation of its Size Dependency	111
<i>Wei-Chen Chen, Chuan-Ding Lin, Horng-Chih Lina, Tiao-Yuan Huang</i>	
Fermi Level Depinning for the Design of III-V FET Source/Drain Contacts	113
<i>Jenny Hu, Ximeng Guan, Donghun Choi, James S. Harris, Krishna Saraswat, H. S. Philip Wong</i>	

Influence of Gate Misalignment on the Electrical Characteristics of MuGFETs	115
<i>Chi-Woo Lee, Aryan Afzalilian, Ran Yan, Nima Dehdashti, Weize Xiong, Jean-Pierre Colinge</i>	
FinFET Resistance Mitigation through Design and Process Optimization	117
<i>Cindy Wang, Josephine Chang, Chung-Hsun Lin, Arvind Kumar, Andreas Gehring, Jin Cho, Amlan Majumdar, Andreas Bryant, Zhibin Ren, Kevin Chan, Thomas Kanarsky, Xinlin Wang, Omer Dokumaci, Michael Guillorn, Marwan Khater, Qingyun Yang, Xi Li, Munir Naeem, Judson Holt, Yongsik Moon, John King, John Yates, Ying Zhang, Dae-gyu Park, Christine Ouyang, Wilfried Haensch</i>	
Sub-100μW Low Power Operation of Vibrating Body FETs	119
<i>Daniel Grogg, Adrian Mihai Ionescu</i>	
Inversion-channel GaN MOSFET Using Atomic-layer-deposited Al₂O₃ as Gate Dielectric	121
<i>Y. C. Chang, W. H. Chang, H. C. Chiu, Y. H. Chang, L.T. Tung, C. H. Lee, M. Hong, J. Kwo, J. M. Hong, C. C. Tsai</i>	
A Comparison Study of Silicon Nanowire Transistor with Schottky-Barrier Source/Drain and Doped Source/Drain	123
<i>Zhaoyi Kang, Liangliang Zhang, Runsheng Wang, Ru Huang</i>	
High Mobility SiGe Shell-Si Core Omega Gate pFETs	125
<i>Hemant Adhikari, Harlan R. Harris, Casey E. Smith, Ji-Woon Yang, Brian Coss, Srivatsan Parthasarathy, Bich-Yen Nguyen, Paul Patrino, Tejas Krishnamohan, Ian Cayrefourcq, Prashant Majhi, Raj Jammy</i>	
Metal-Oxide-Semiconductor Devices with UHV-Ga₂O₃(Gd₂O₃) on Ge(100)	128
<i>L. K. Chu, T. D. Lin, C. H. Lee, L. T. Tung, W. C. Lee, R. L. Chu, C. C. Chang, M. Hong, J. Kwo</i>	
Self-aligned Inversion Channel In_{0.53}Ga_{0.47}As N-MOSFETs with ALD-Al₂O₃ and MBE Al₂O₃/Ga₂O₃(Gd₂O₃) as Gate Dielectrics	130
<i>H. C. Chiu, T. D. Lin, P. Chang, W. C. Lee, C. H. Chiang, J. Kwo, Y. S. Lin, Shawn S. H. Hsu, W. Tsai, M. Hong</i>	
Inversion-Type Surface Channel In_{0.53}Ga_{0.47}As Metal-Oxide-Semiconductor Field-Effect Transistors with Metal-Gate/High-k Dielectric Stack and CMOS-Compatible PdGe Contacts	132
<i>Hock-Chun Chin, Xinke Liu, Leng-Seow Tan, Yee-Chia Yeo</i>	
Sub-100nm High-K Metal Gate GeOI pMOSFETs Performance: Impact of the Ge Channel Orientation and of the Source Injection Velocity	134
<i>C. Le Royer, A. Pouydebasque, K. Romanjek, V. Barral, M. Vinet, J.-M. Hartmann, E. Augendre, H. Grampeix, L. Lachal, C. Tabone, B. Previtali, R. Truche, F. Allain</i>	
Tri-gated Poly-Si Nanowire SONOS Devices	136
<i>Hsing-Hui Hsu, Ta-Wei Liu, Chuan-Ding Lin, Chiu Kuo-Jung, Tiao-Yuan Huang, Horng-Chih Lin</i>	
Overall Operation Considerations for a SONOS-based Memory	138
<i>C. H. Lee, W. H. Tu, L. H. Chong, S. H. Gu, K.F. Chen, Y. J. Chen, J. Y. Hsieh, I. J. Huang, N. K. Zous, T. T. Han, M. S. Chen, W. P. Lu, K. C. Chen, Tahui Wang, C. Y. Lu</i>	
Reliability Study of MANOS with and without a SiO₂ Buffer Layer and BE-MANOS Charge-Trapping NAND Flash Devices	140
<i>Chien-Wei Liao, Sheng-Chih Lai, Hang-Ting Lue, Ming-Jui Yang, Chin-Yen Shen, Yi-Hsien Lue, Yu-Fong Huang, Jung-Yu Hsieh, Szu-Yu, Wang, Guang-Li Luo, Chao-Hsin Chien, Kuang-Yeu Hsieh, Rich Liu, Chih-Yuan Lu</i>	
Reliability of Planar and FinFET SONOS Devices for NAND Flash Applications – Field Enhancement vs. Barrier Engineering	142
<i>Tzu-Hsuan Hsu, Hang-Ting Lue, Sheng-Chih Lai, Ya-Chin King, Kuang-Yeu Hsieh, Rich Liu, Chih-Yuan Lu</i>	

**Band Engineered Tunnel Oxides for Improved TANOS-type Flash Program/Erase with
Good Retention and 100K Cycle Endurance** 144
*David C. Gilmer, Niti Goel, Sarves Verma, Hokyung Park, Chanro Park, Gennadi Bersuker, Paul D.
Kirsch, Krishna C. Saraswat, Raj Jammy*

Author Index